



Attorney Docket No. ASC-049C1  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Eugene A. Fitzgerald

Application No. 10/774,890

Filed: February 9, 2004

Art Unit: 2818

Title: RELAXED SIGE PLATFORM FOR HIGH  
SPEED CMOS ELECTRONICS AND HIGH  
SPEED ANALOG CIRCUITS

Examiner: D. A. Le

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

In accordance with 37 CFR 1.98(a)(2)(ii), Applicant has not submitted copies of U.S. patents and U.S. patent applications. Applicant submits herewith copies of foreign patents and non-patent literature in accordance with 37 CFR 1.98(a)(2).

Applicants hereby apprise the Examiner of the reexamination, and Office actions issued therein, of the patent to which this application claims priority, U.S. Patent No. 6,703,688.

03/05/2007 CNGUYEN2 00000042 10774890

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This Information Disclosure Statement is filed after the mailing date of the first Office Action on the merits, but before the mailing date of a Final Office Action or Notice of Allowance (37 CFR 1.97(c)).

Our check in the amount of \$180.00 covering the fee set forth in 37 CFR 1.17(p) is enclosed. The Director is hereby authorized to charge any deficiency in the filed fees to our Deposit Account No. 07-1700, under Order No. ASC-049C1.

Date: Feb. 28, 2007

Respectfully submitted,

By Natasha Us

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PTO/SB/08A/B (09-06)

Approved for use through 03/31/2007. OMB 0651-0031

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| Substitute for form 1449/PTO   |   |    | <b>Complete if Known</b> |                        |           |
| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br><i>(Use as many sheets as necessary)</i> |   |    | Application Number       | 10/774,890             |           |
|  |   |    | Filing Date              | February 9, 2004       |           |
|  |   |    | First Named Inventor     | Eugene A. Fitzgerald   |           |
|  |   |    | Art Unit                 | 2818                   |           |
|  |   |    | Examiner Name            | D. A. Le               |           |
| Sheet  | 1 | of | 11                       | Attorney Docket Number | ASC-049C1 |

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|                          |                          | Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known) |  |                                   |  |   |   |
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| NON PATENT LITERATURE DOCUMENTS |                          |  |  |  |
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|  |    |    |    | Application Number       | 10/774,890           |
|  |    |    |    | Filing Date              | February 9, 2004     |
|  |    |    |    | First Named Inventor     | Eugene A. Fitzgerald |
|  |    |    |    | Art Unit                 | 2818                 |
|  |    |    |    | Examiner Name            | D. A. Le             |
| Sheet  | 10 | of | 11 | Attorney Docket Number   | ASC-049C1            |

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